ME2D5R030SLP

MOSFETs Silicon 30V N-Channel MOS

Applications

- Synchronus Rectification
- Industrial and Motor Drive
- DC/DC and AC/DC Converters
- Power Tools

Product Summary

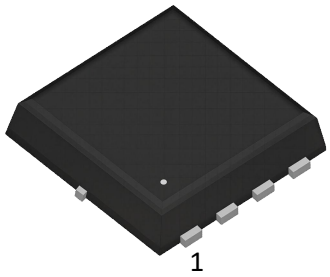
V_{DS}	30	V
I_D	115	A
$R_{DS(ON)}$,Typ@10V	2.2	mΩ
$R_{DS(ON)}$,Typ@4.5V	2.8	mΩ
Q_g	35	nC

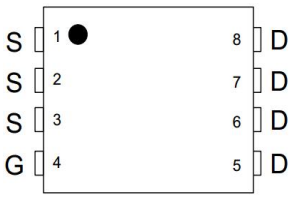
Features

- High-Speed Switching
- Low $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS and RG Tested

RoHS Pb Lead-free HF

DFN3x3





Gate： 4
Drain：5-8
Source：1-3

Package Marking and Ordering Information

Ordering code	Marking	Package	Packaging	Min. package quantity
ME2D5R030SLP	2D503SL	DFN3x3	Tape & Reel	5000

Absolute Maximum Ratings（Tc=25℃ unless otherwise noted)

Parameter			Symbol	Ratings	Unit
Drain-Source Voltage			V_{DS}	30	V
Gate-Source Voltage			V_{GS}	±20	V
Continuous Drain Current	Tc=25℃	(Note 1)	I_D	115	A
Continuous Drain Current	Tc=100℃	(Note 1)		75	A
Drain Current-Pulsed		(Note 1)	I_{DM}	300	A
Total Dissipation			P_D	55	W
Junction Temperature			T_j	150	℃
Storage Temperature			T_{stg}	-55-150	℃
Single Pulse Avalanche Energy		(Note 2)	E_{AS}	53	mJ

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Thermal Characteristics

Parameter	Symbol	Max	Unit
Maximum Junction-to-Case	$R_{\theta JC}$	2.2	℃/W
Maximum Junction-to-Ambient	$R_{\theta JA}$	50	℃/W

Note 1：Ensure that the channel temperature does not exceed 150℃.

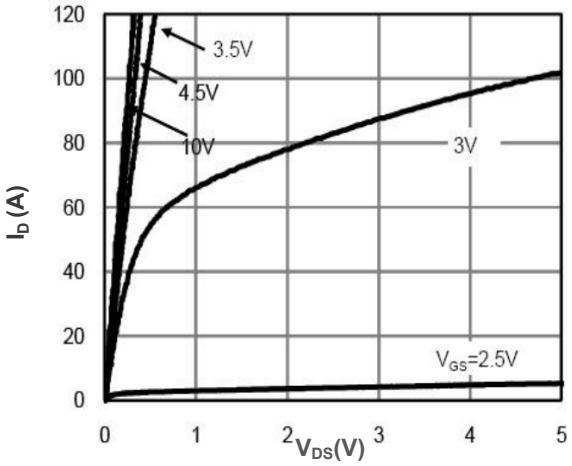
Note 2：V_{DD}=40V, Tch= 25℃(initial), L=0.5mH, R_g=25Ω.

Note：This transistor is sensitive to electrostatic discharge and should be handled with care.

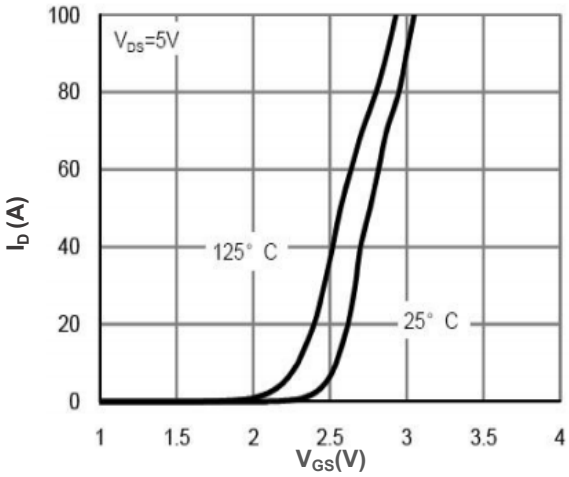
Electrical Characteristics（Tc=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static Parameters						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=250uA	30	-	-	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V	-	-	1	uA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS}=V_{DS},I_D=250uA	1.0	1.6	2.2	V
Drain-Source On Resistance	$R_{DS(ON)}$	V_{GS}=4.5V,I_D=15A	-	2.8	3.2	mΩ
		Tj=125℃	-	4.1	-	
		V_{GS}=10V,I_D=20A	-	2.2	2.5	mΩ
		Tj=125℃	-	3.3	-	
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=15V,V_{GS}=0V, f=1.0MHz	-	2399	-	pF
Output Capacitance	C_{oss}		-	1133	-	pF
Reverse Transfer Capacitance	C_{rss}		-	54	-	pF
Gate Resistance	R_g	V_{DS}=0V,V_{GS}=0V, f=1.0MHz	-	2.7	-	Ω
Switching Paramters						
Turn-On Delay Time	$t_{d(on)}$	V_{DS}=15V,I_D=20A, V_{GS}=10V,R_G=1.6Ω	-	8	-	ns
Turn-On Rise Time	t_r		-	4	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	37	-	ns
Turn-Off Fall Time	t_f		-	8	-	ns
Total Gate Charge	Q_g	V_{DS}=15V,I_D=20A, V_{GS}=10V	-	35	-	nC
Gate-Source Charge	Q_{gs}		-	6	-	nC
Gate-Drain Charge	Q_{gd}		-	5	-	nC
Source-Drain Characteristics						
Diode Forward Voltage	V_{sd}	V_{GS}=0V,I_S=10A	-	0.8	1.2	V
Reverse Recovery Time	t_{rr}	V_R=15V,I_F=65A, di/dt=100A/us	-	14	-	ns
Reverse Recovery Charge	Q_{rr}		-	21	-	nC

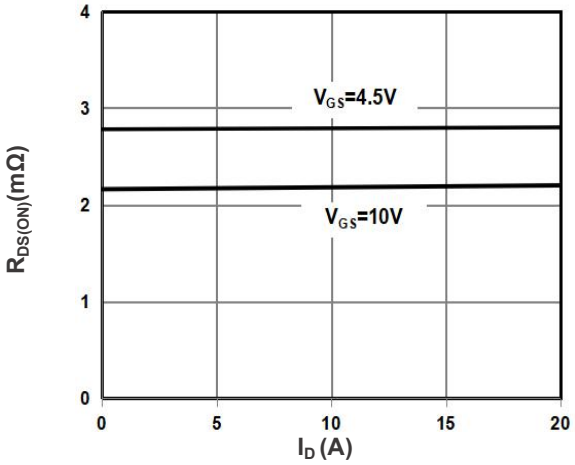
Characteristics Curves



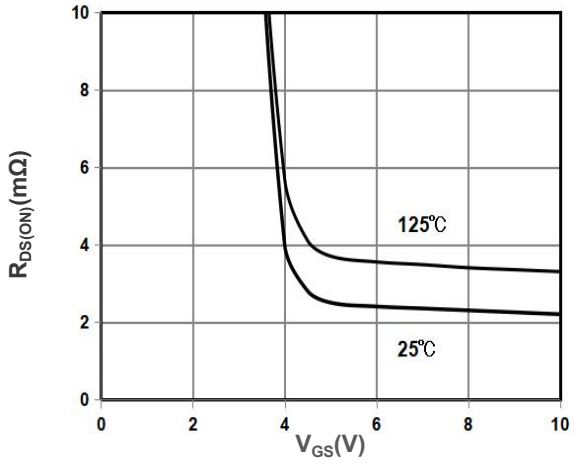
Output Characteritsics



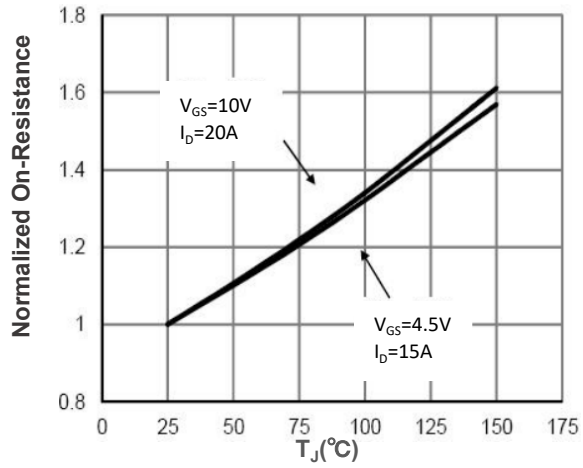
Transfer Characteritsics



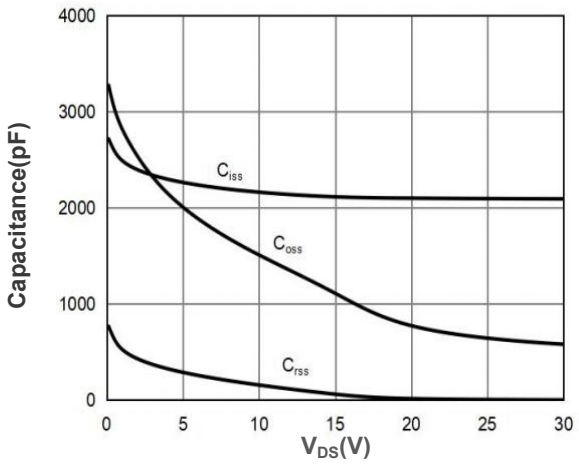
On Resistance Vs Drain Current



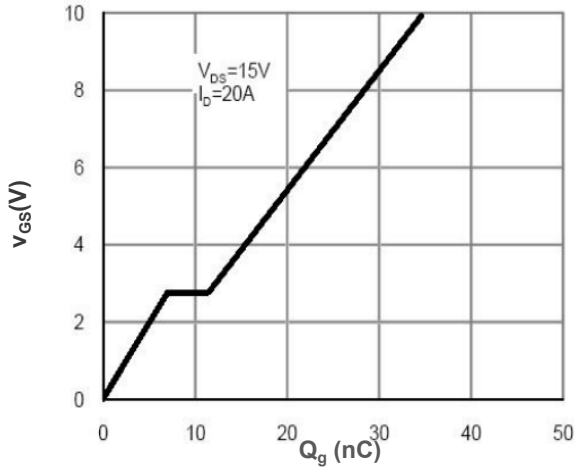
On Resistance Vs Gate Source Voltage



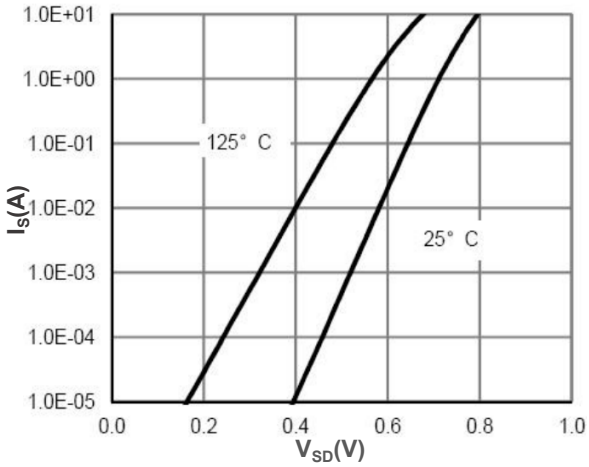
Rdson-JunctionTemperature



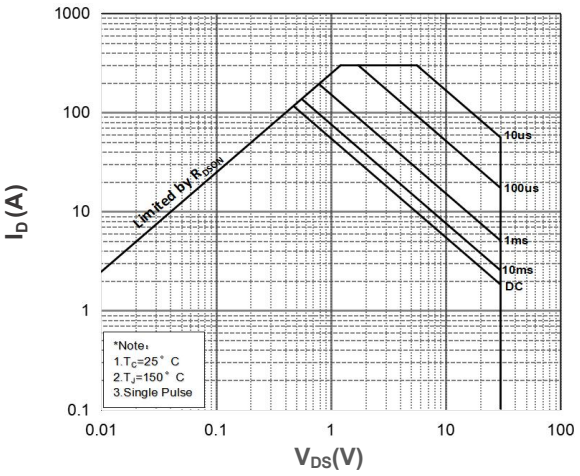
Capacitance



Gate Charge Waveform



Source-Drain Diode Forward Voltage

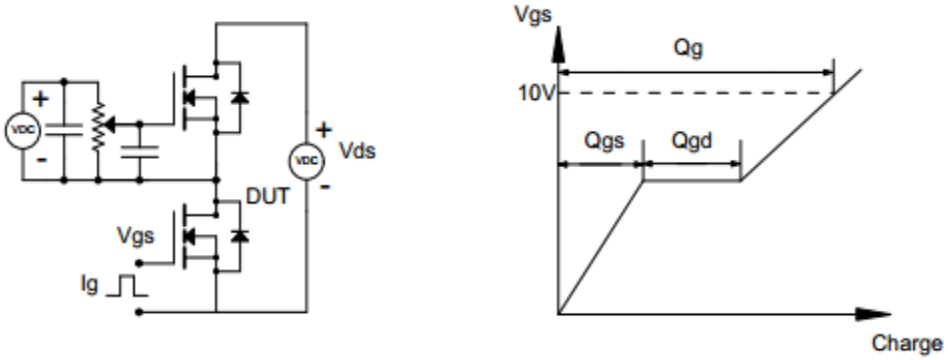


Maximum Safe Operating Area

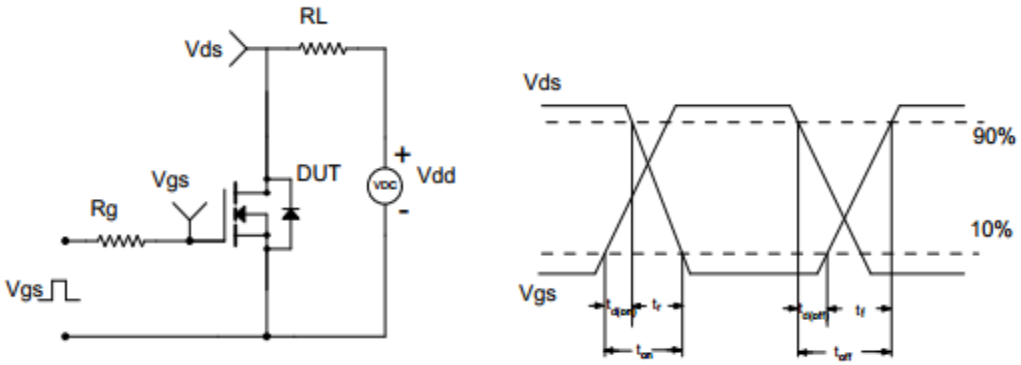
Note： The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Test Circuit & Waveform

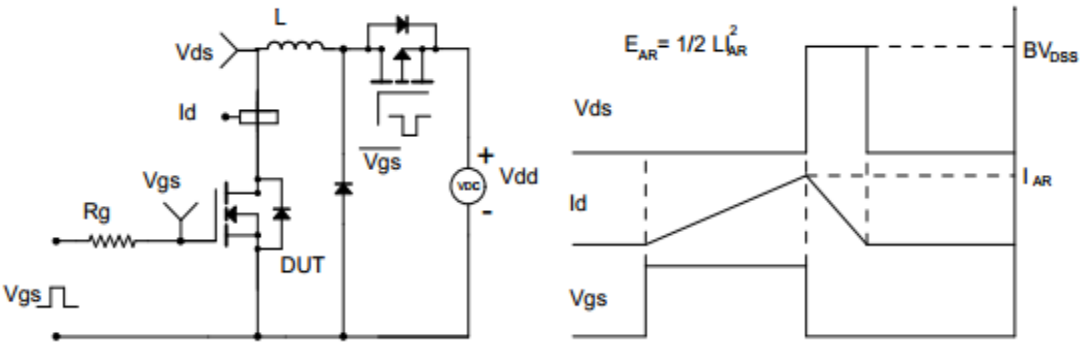
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveform



DFN3x3 Package Dimensions

Unit：mm

Symbol	Min	Nom	Max	Symbol	Min	Nom	Max
A	0. 7	0. 8	0. 9	e	0. 55	0. 65	0. 75
b	0. 2	0. 30	0. 4	H1	0. 345	0. 545	0. 745
C	0. 1	0. 15	0. 2	H2	0. 25	0. 45	0. 65
D	3. 00	3. 10	3. 20	K		0. 67	
D1	2. 35	2. 45	2. 55	L1		0. 15	
E	3. 00	3. 10	3. 20	L2		0. 15	
E1	3. 2	3. 4	3. 6	N	0	–	0. 1
E2	1. 635	1. 735	1. 835				

